

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

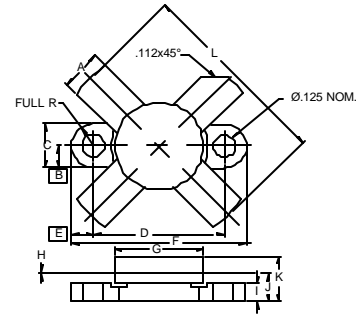
The **ASI HFT150-28** is Designed for

**FEATURES:**

- $P_G = 16$  dB min. at 150 W/30 MHz
- $IMD_3 = -28$  dBc max. at 150 W<sub>(PEP)</sub>
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_D$	16 A
$V_{(BR)DSS}$	65 V
$V_{GS}$	$\pm 40$ V
$P_{DISS}$	300 W @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+200^\circ C$
$T_{STG}$	$-65^\circ C$ to $+150^\circ C$
$q_{JC}$	$0.60^\circ C/W$

**PACKAGE STYLE .500 4L FLG**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.125 / 3.18	
C	.245 / 6.22	.255 / 6.48
D	.720 / 18.28	.730 / 18.54
E	.125 / 3.18	
F	.970 / 24.64	.980 / 24.89
G	.495 / 12.57	.505 / 12.83
H	.003 / 0.08	.007 / 0.18
I	.090 / 2.29	.110 / 2.79
J	.150 / 3.81	.175 / 4.45
K	.280 / 7.11	
L	.980 / 24.89	1.050 / 26.67

**ORDER CODE: ASI10616**
**CHARACTERISTICS**  $T_C = 25^\circ C$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$V_{(BR)DSS}$	$V_{GS} = 0$ V $I_{DS} = 100$ mA	65	---	---	V
$I_{DSS}$	$V_{GS} = 0$ V $V_{DS} = 28$ V	---	---	0.5	mA
$I_{GSS}$	$V_{GS} = 20$ V $V_{DS} = 0$ V	---	---	1.0	mA
$V_{GS}$	$V_{DS} = 10$ V $I_D = 100$ mA	1.0	---	5.0	V
$V_{DS}$	$V_{GS} = 10$ V $I_D = 10$ A	---	---	1.5	V
$G_{FS}$	$V_{DS} = 10$ V $I_D = 5$ A	3.5	---	---	mho
$C_{ISS}$ $C_{OSS}$ $C_{RSS}$	$V_{GS} = 28$ V $V_{DS} = 0$ V $F = 1.0$ MHz	---	375 188 26	---	pF
$P_{IN}$ $G_{PS}$ $h$	$V_{DD} = 28$ V $I_{DQ} = 250$ mA $P_{OUT} = 150$ W (PEP) $f = 175$ MHz	50	10	15	W dB %